

PDFN5×6 N
N-Channel MOSFET in a PDFN5×6 Plastic Package .

AEC-Q101

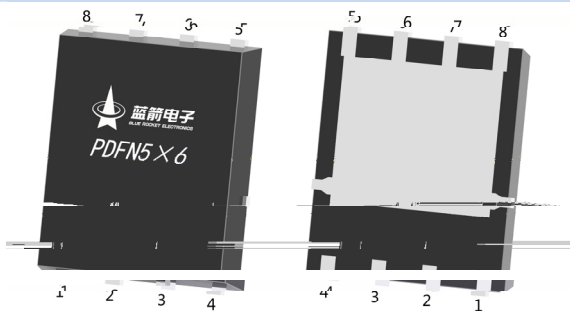
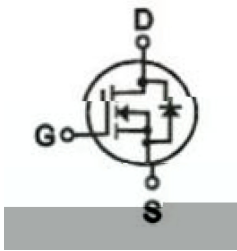
Low $R_{DS(ON)}$ to minimize conductive loss, low Gate Charge for fast switching, Low Thermal resistance, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

MB/NB/UMPC/VGA

Buck

—

Battery Management, High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA, Networking DC-DC Power System, Load Switch, Meet the stringent requirements of automotive applications.



PIN1、 2、 3: S PIN4: G PIN5、 6、 7、 8: D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D

- See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	30	V
Drain Current - Continuous		I _D	146	A
Drain Current – Pulsed		I _{DM}	300	A
Gate-Source Voltage		V _{GS}	± 20	V
Power Dissipation		P _D (T _c =25°C)	57	W
Single Pulse Avalanche Energy(L=0.5mH)		E _{AS}	315	mJ
Avalanche Current(L=0.5mH)		I _{AS}	30	A
Junction and Storage Temperature Range		T _j , T _{stg}	-55 to 150	
Thermal resistance, junction - ambient	t ≤ 10s	R _{θ JA}	20	°C/ W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	R _{θ JC}	2.2	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.6	3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=24\text{A}$		1.5	1.8	m Ω
		$V_{GS}=4.5\text{V}, I_D=12\text{A}$		2.0	2.8	
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.68	1	V
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		8500		pF
Output Capacitance	C_{oss}			890		
Reverse Transfer Capacitance	C_{rss}			670		
Gate resistance	R_g	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		1.8		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}, V_{DS}=15\text{V},$ $I_D=20\text{A}$		60		nC
Total Gate Charge	$Q_{g(4.5V)}$			28		
Gate Source Charge	Q_{gs}			12		
Gate Drain Charge	Q_{gd}			9.5		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\ \Omega$ $R_{GEN}=3\ \Omega$		12.5		ns
Turn-On Rise Time	t_r			6.0		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	t_f			10.5		

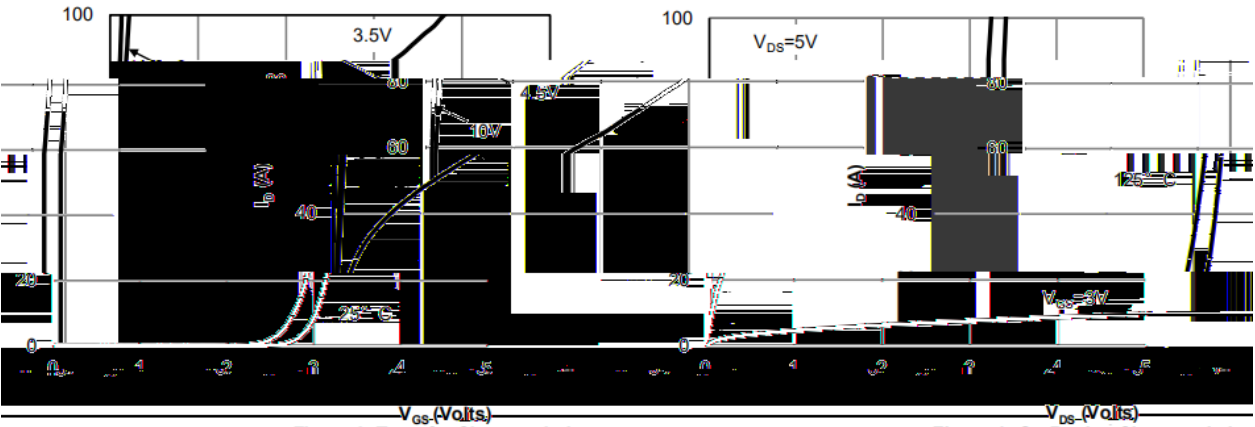


Figure 2: Transfer Characteristics

Figure 1: On-Region Characteristics

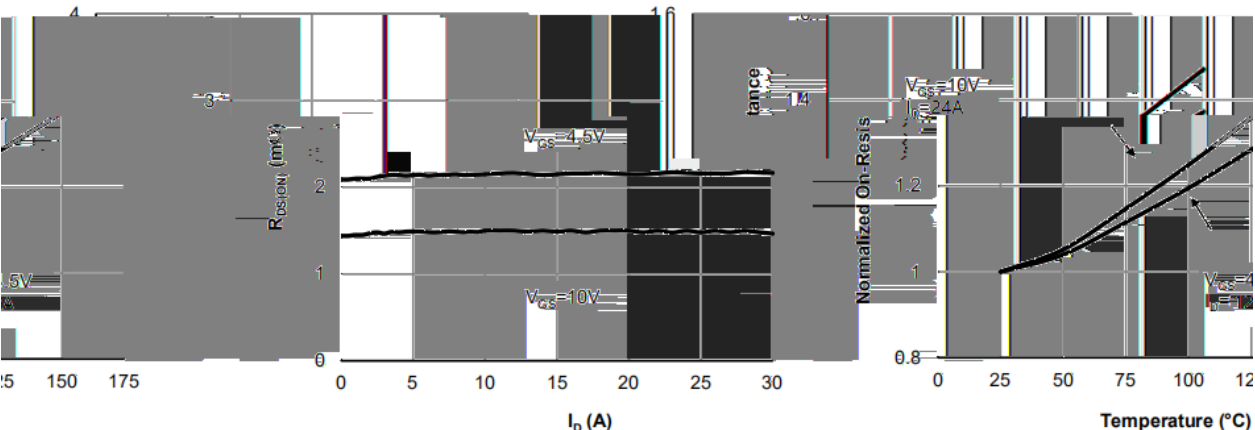


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature

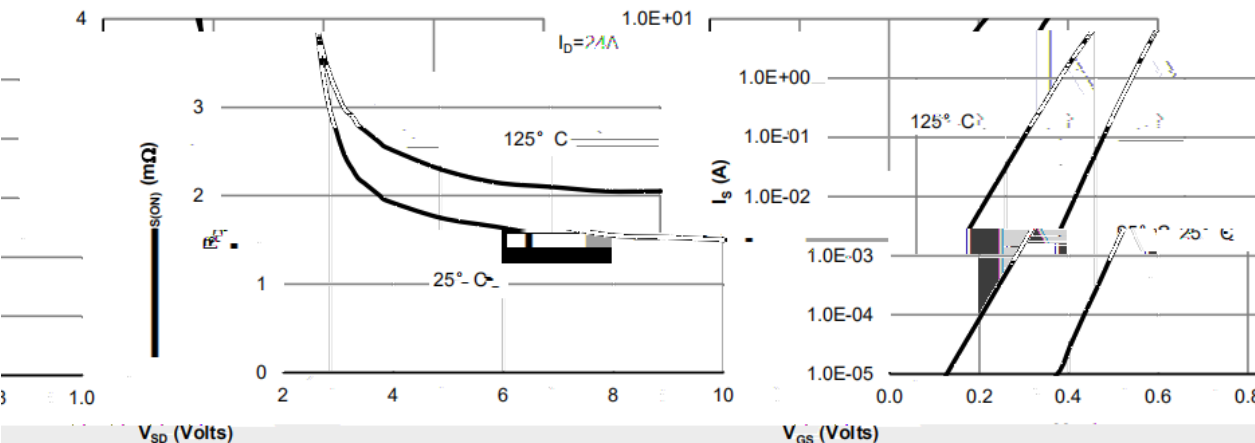


Figure 6: Body-Diode Characteristics

Figure 5: On-Resistance vs. Gate-Source Voltage

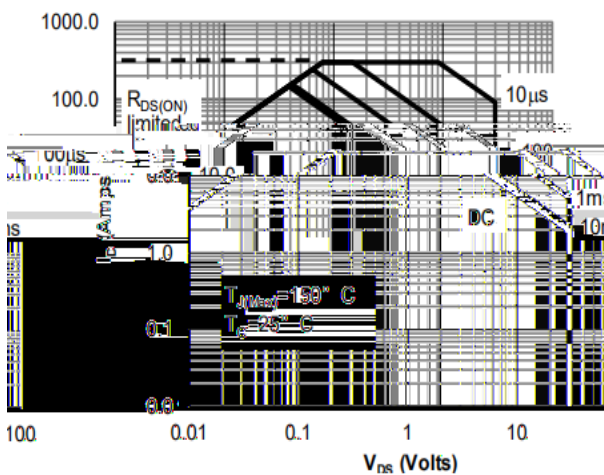
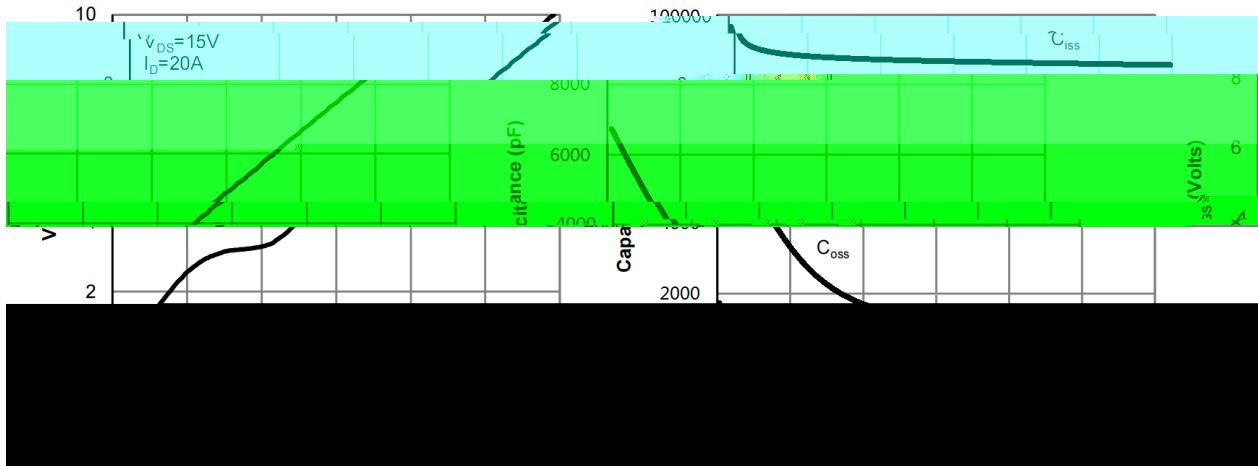


Figure 9: Maximum Forward Biased Safe Operating Area

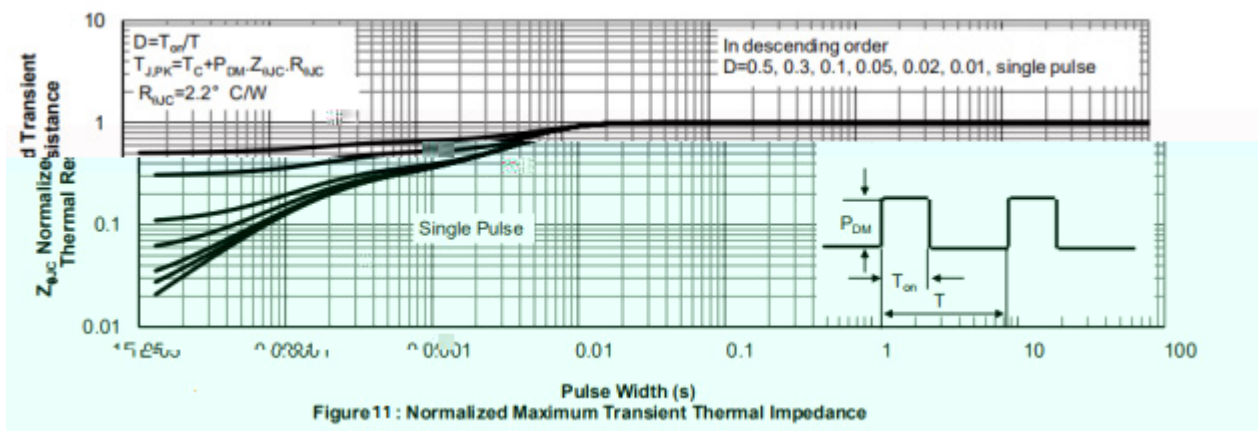
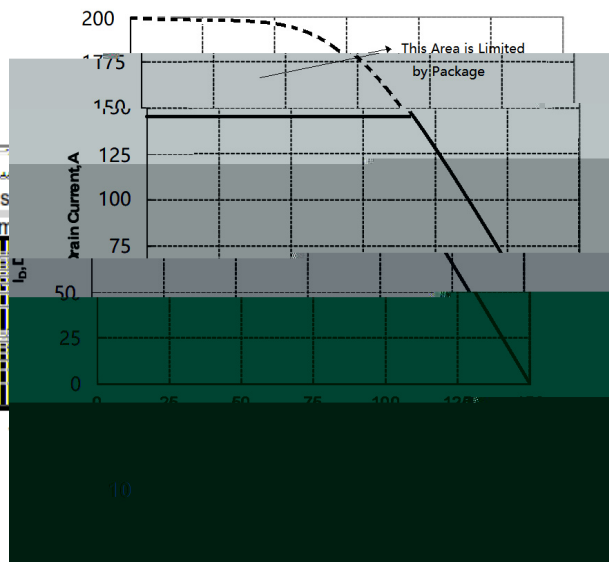
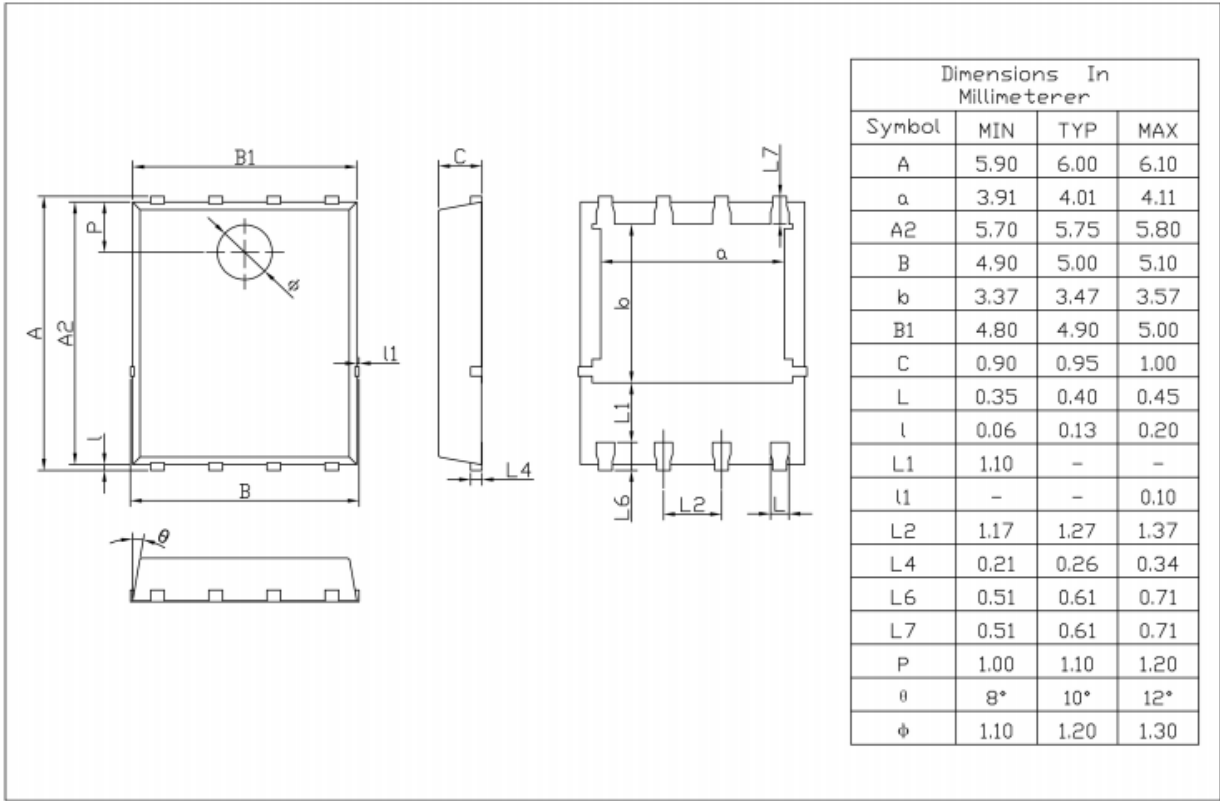


Figure11: Normalized Maximum Transient Thermal Impedance

PDFN5 X6

Unit:mm



Rev.00 201812



BR

Q

016N03

Note:

BR: Company Code

Q: Automobile halogen-free product Code

016N03: Product Type Code

****: Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1

150 200

60 120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

255±5